Ordering number: EN 2391

SANYO

No. 2391

2SK771

N-Channel Junction Silicon FET

Low-Frequency General-Purpose Amp Applications

Applications

- Variable resistors, analog switches, AF amp, constant-current circuit

Features

- Adoption of FBET process
- Very small-sized package permitting sets to be made smaller and slimmer

Absolute Maximum Ratings at Ta=25°C

			unit
Drain to Source Voltage	V_{DSX}	40	V
Gate to Drain Voltage	V_{GDS}	-40	V
Gate Current	I_G	10	mA
Drain Current	I_D	20	mA
Allowable Power Dissipation	P_D	200	mW
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55 to +150	°C

Electrical Characteristics at Ta=25°C

			min	typ	max	unit
Gate to Drain Breakdown Voltage	$V_{(BR)GDS}$	I_G=-10μA, V_{DS}=0	-40			V
Gate Cutoff Current	I_{GSS}	V_{GS}=-20V, V_{DS}=0			-1.0	nA
Cutoff Voltage	$I_{GS(off)}$	V_{DS}=10V, I_D=1μA	-0.3	-0.9	-2.5	V
Drain Current	I_{DSS}	V_{DS}=10V, V_{GS}=0	1.2*		12.0*	mA
Forward Transfer Admittance	$\|Y_{fs}\|$	V_{DS}=10V, V_{GS}=0, f=1kHz	4.5	9.0		mS
Input Capacitance	c_{iss}	V_{DS}=10V, V_{GS}=0, f=1MHz		9.0		pF
Reverse Transfer Capacitance	c_{rss}	V_{DS}=10V, V_{GS}=0, f=1MHz		2.1		pF
Noise Figure	NF	V_{DS}=10V, Rg=1kΩ, I_D=1mA, f=1kHz		1.5		dB

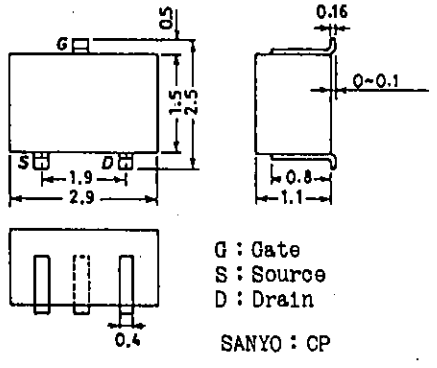
*: The 2SK771 is classified by I_{DSS} as follows (unit:mA):

1.2 3 3.0	2.5 4 6.0	5.0 5 12.0

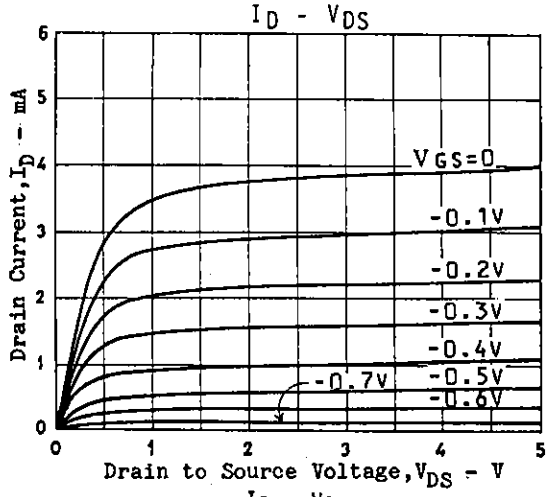
Marking : FJ

h_{FE} rank: 3,4,5

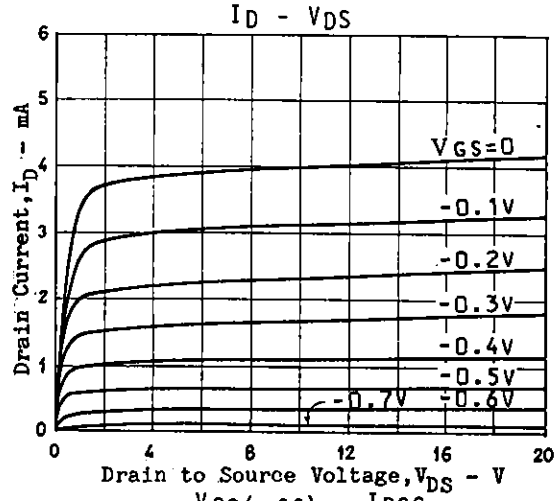
Package Dimensions 2050
(unit:mm)



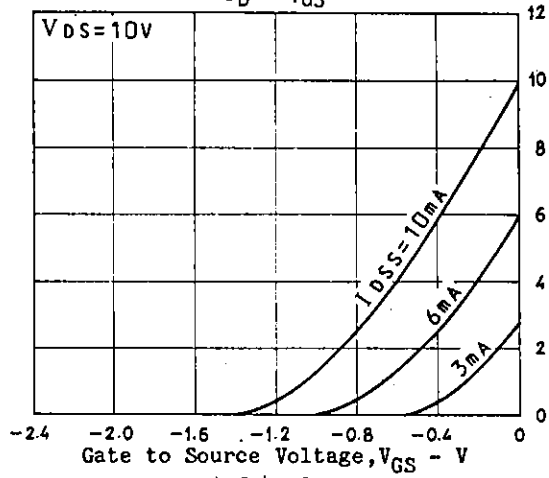
I_D - V_{DS}



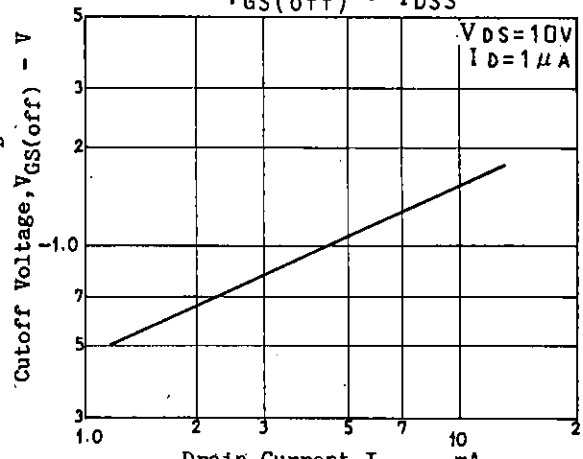
I_D - V_{DS}



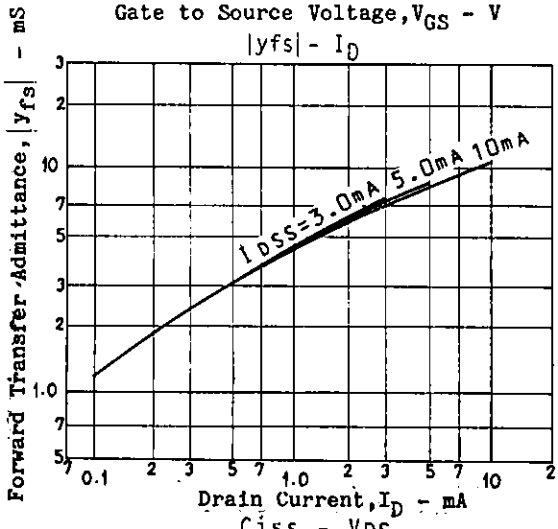
I_D - V_{GS}



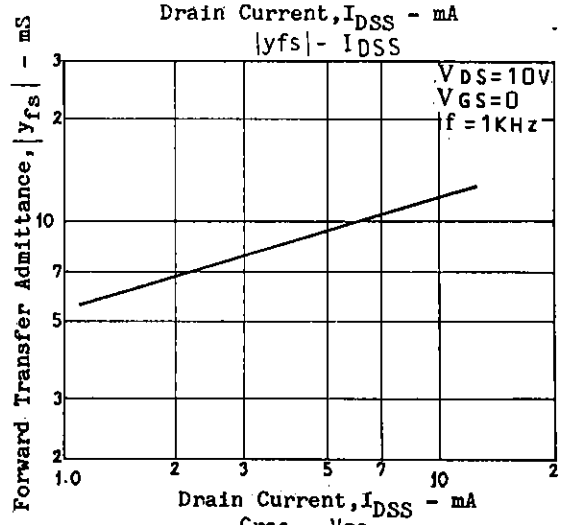
$V_{GS(off)}$ - I_{DSS}



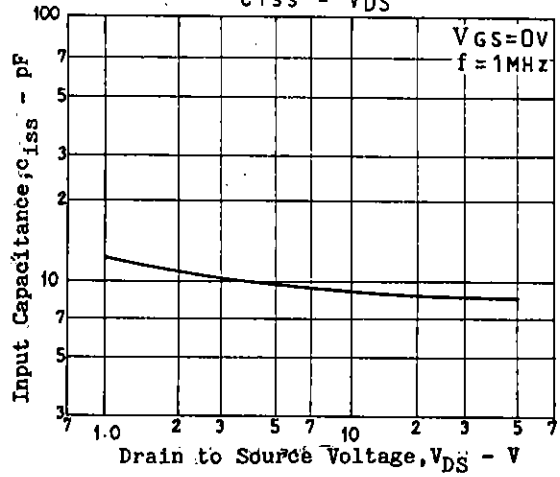
|yfs| - I_D



|yfs| - I_{DSS}



Ciss - V_{DS}



Crss - V_{DS}